

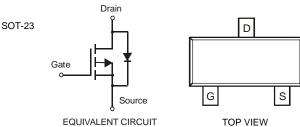
P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance:
 - $\begin{array}{l} R_{DS(ON)} < 100m\Omega @ V_{GS} = -4.5V, \ I_{D} = -2.7A \\ R_{DS(ON)} < 215m\Omega @ V_{GS} = -2.5V, \ I_{D} = -2.0A \end{array}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Char	acteristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Drain Current (Note 1)	Steady State	T _A = 25°C T _A = 70°C	ID	-2.7 -2	A
Pulsed Drain Current (Note 3)			I _{DM}	8	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	PD	1.08	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 1)	$R_{ heta}JA$	115	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes: 1. Device mounted on FR-4 PCB. t \leq 5 sec.

2. No purposefully added lead.

3. Pulse width $\leq 10\mu S$, Duty Cycle $\leq 1\%$.

4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

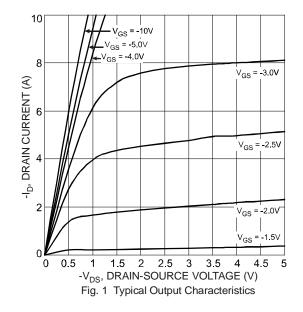
TOP VIEW

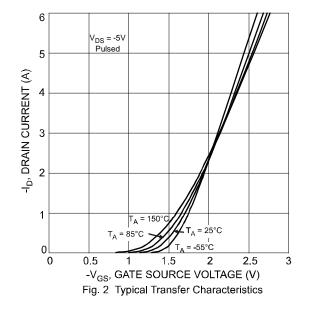


Electrical Characteristics @T_A = 25°C unless otherwise specified

			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	-					
Drain-Source Breakdown Voltage	BV _{DSS}	-20		—	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}			-800	nA	$V_{DS} = -20V, V_{GS} = 0V$
On-State Drain Current	la var n	-6			А	$V_{DS} \leq \text{-}5V, \ V_{GS} = \text{-}4.5V$
	I _{D(ON)}	-3			^	$V_{DS} \leq$ -5V, V_{GS} = -2.5V
Gate-Source Leakage	lass	_	—	±80	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
	I _{GSS}			±800	ПА	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)				-		
Gate Threshold Voltage	V _{GS(th)}	-0.62	-0.89	-1.25	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	Pag (gu)	_	80 165	100	mΩ	$V_{GS} = -4.5V, I_D = -2.7A$
	R _{DS (ON)}			215		$V_{GS} = -2.5V, I_D = -2.0A$
Forward Transfer Admittance	Y _{fs}		4		S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage (Note 5)	V _{SD}			-1.26	V	$V_{GS} = 0V, I_{S} = -2.7A$
DYNAMIC CHARACTERISTICS				_	_	
Input Capacitance	Ciss	_	250	—	pF	
Output Capacitance	C _{oss}		88	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		58		pF	
Gate Resistance	Rg	_	12	16	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$
Total Gate Charge	Qg		4.3	5.3		V _{GS} = -4.5V, V _{DS} = -10V,
Gate-Source Charge	Q _{gs}		0.9		nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_{D} = -2.7A$
Gate-Drain Charge	Q _{gd}		2.1			

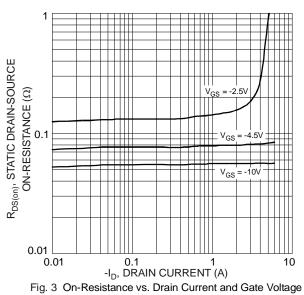
Notes: 5. Short duration pulse test used to minimize self-heating effect.

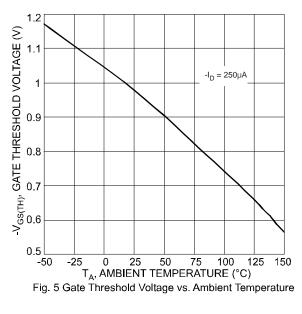


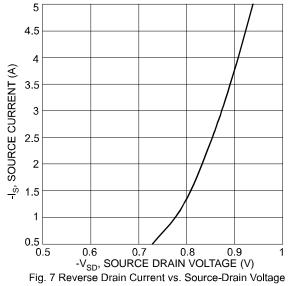


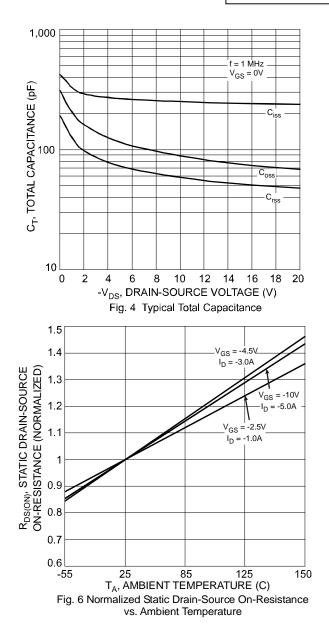


NEW PRODUCT









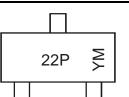


Ordering Information (Note 6)

Part Number	Case	Packaging
DMP2215L-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

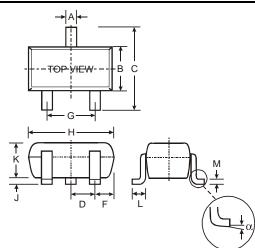


22P = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Coc	

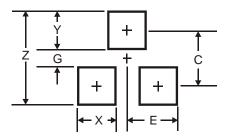
Date Code Key												
Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	ι	J	١	/	V	V)	X		(2	7
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-23						
Dim	Min Max					
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89 1.03					
F	0.45 0.60					
G	1.78	2.05				
Н	2.80	3.00				
J	0.013 0.10					
K	0.903 1.10					
L	0.45 0.61					
Μ	0.085 0.180					
α	0°	8°				
All Dir	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
С	2.0
E	0.9

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